









CEU11P10

-100V ▲ 220mΩ ▲ -7A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type P-channel enhancement mode UL94V-0 rated flame retardant epoxy TO252 (DPAK) package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)}

High power and current handling capability

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current	I _D	-7A
Pulsed Drain Current Note 1	I _{DM}	-28A
Maximum Power Dissipation at T _C = 25°C	P _D	31W
Power Dissipation Derating above 25°C	ΔP _D	0.25W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

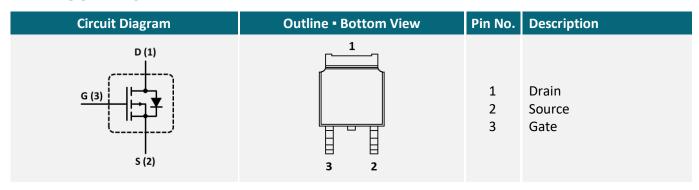
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	4°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	50°C/W

APPLICATIONS

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
			+	Ŷ

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

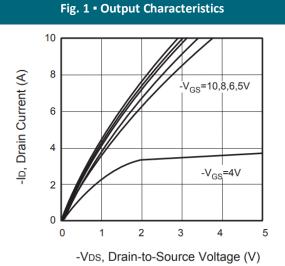
Item	Condition	Symbol	Min.	Тур.	Max.	Unit		
Off Characteristics								
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250\mu A$	BV_{DSS}	-60			V		
Zero Gate Voltage Drain Current	$V_{DS} = -100V$, $V_{GS} = 0V$	I _{DSS}			-1	μΑ		
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA		
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA		
On Characteristics Note 4								
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250 \mu A$	$V_{GS(th)}$	-2		-4	V		
Static Drain-Source On-Resistance	V_{GS} = -10V, I_D = -4A	R _{DS(ON)}		220	270	mΩ		
Dynamic Characteristics Note 4								
Input Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		680		pF		
Output Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		100		pF		
Reverse Transfer Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz	C_{RSS}		60		pF		
Switching Characteristics Note 4								
Turn-On Delay Time	V_{DD} = -80V, V_{GS} = -10V, I_D = -7A, $R_{G(ext)}$ = 6Ω	t _{D(ON)}		13		ns		
Turn-On Rise Time	V_{DD} = -80V, V_{GS} = -10V, I_D = -7A, $R_{G(ext)}$ = 6Ω	t _R		7		ns		
Turn-Off Delay Time	V_{DD} = -80V, V_{GS} = -10V, I_D = -7A, $R_{G(ext)}$ = 6Ω	t _{D(OFF)}		29		ns		
Turn-Off Fall Time	V_{DD} = -80V, V_{GS} = -10V, I_D = -7A, $R_{G(ext)}$ = 6Ω	t _F		5		ns		
Total Gate Charge	$V_{DS} = -80V$, $V_{GS} = -10V$, $I_{D} = -7A$	Q_{G}		16		nC		
Gate Source Charge	$V_{DS} = -80V$, $V_{GS} = -10V$, $I_{D} = -7A$	Q_{GS}		2		nC		
Gate Drain Charge	$V_{DS} = -80V$, $V_{GS} = -10V$, $I_D = -7A$	Q_{GD}		6		nC		
Drain-Source Diode Characteristics and Maximum Ratings								
Drain-Source Diode Forward Current Note 2		Is			-7	Α		
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$, $I_S = -1A$	V_{SD}			-1.2	V		

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10sec.
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



-VGS, Gate-to-Source Voltage (V)

Fig. 2 • Transfer Characteristics

Fig. 3 • Capacitance 780 650 C_{iss} C, Capacitance (pF) 520 390 260 Coss 130 0 3 6 9 12 0 15 -VDS, Drain-to-Source Voltage (V)

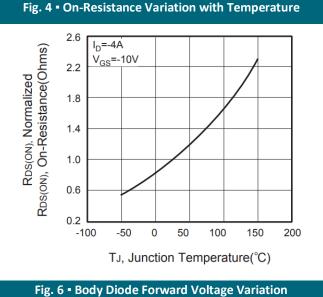
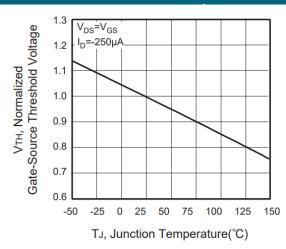
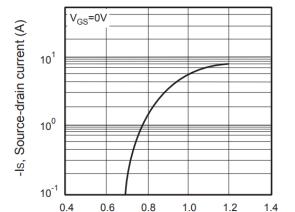


Fig. 5 • Gate Threshold Variation with Temperature





-Vsp, Body Diode Forward Voltage (V)

with Source Current

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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

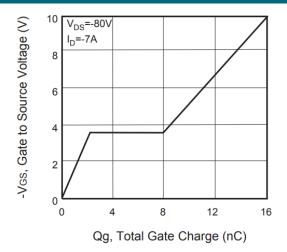


Fig. 8 • Maximum Safe Operating Area

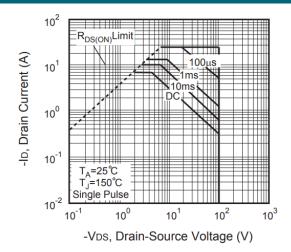


Fig. 9 • Breakdown Voltage Variation vs. Temperature

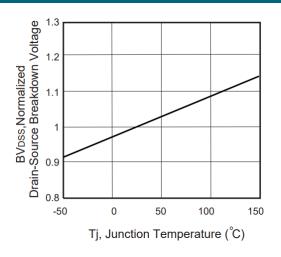


Fig. 10 • Switching Test Circuit

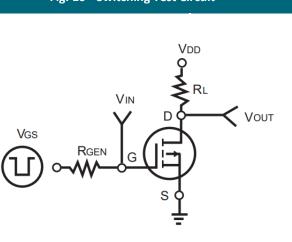
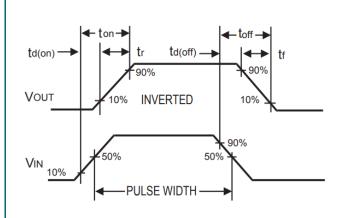


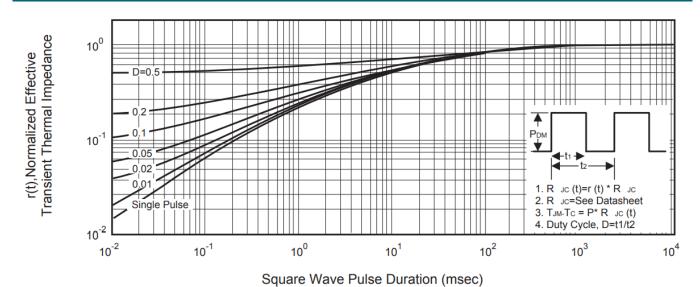
Fig. 11 • Switching Waveforms





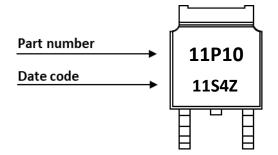
REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve



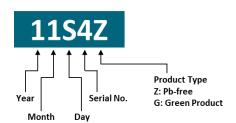


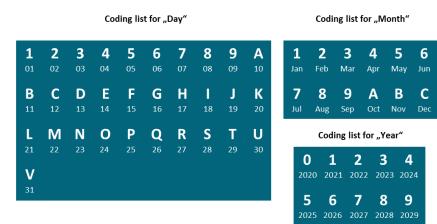
PART MARKING



DATE CODE

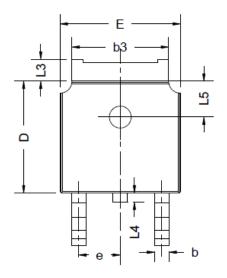
Example: 11S4Z

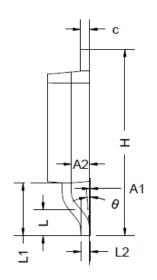


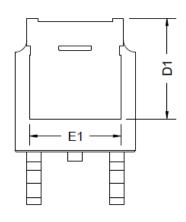


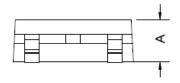


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
Α	2.20	2.30	2.38			
A1	0.00	-	0.20			
A2	0.90 1.07		1.17			
b	0.68	0.78	0.90			
b3	5.23	5.33	5.46			
С	0.43	0.53	0.61			
D	5.98	6.10	6.22			
D1	5.30 REF					
Е	6.40	6.60	6.73			
E1	4.63	-	-			

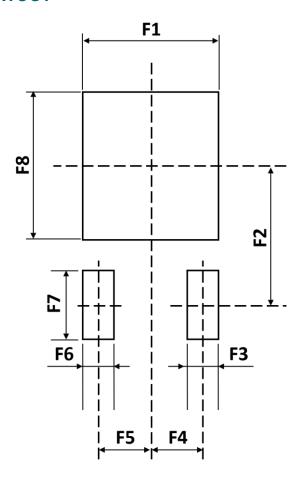
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)				
е		2.286 BSC					
Н	9.40	10.10	10.50				
L	1.38	1.50	1.75				
L1	2.90 REF						
L2		0.51 BSC					
L3	0.88	-	1.28				
L4	0.50		1.00				
L5	1.65	1.80	1.95				
θ	0°	-	8°				

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEU11P10	TO252 (DPAK)	Reel	2,500pcs	5,000pcs	40,000pcs



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-
F2	-	6.25	-
F3	-	1.40	-
F4	-	2.29	-

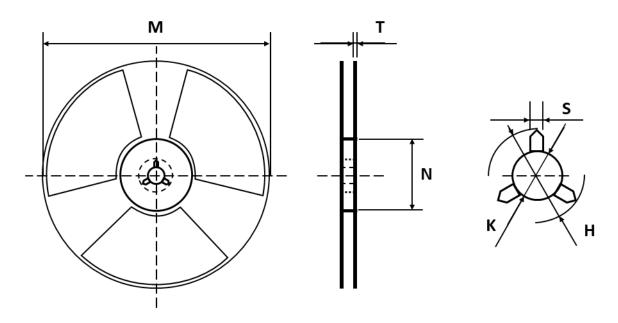
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.29	-
F6	-	1.40	-
F7	-	3.00	-
F8	-	6.50	-

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

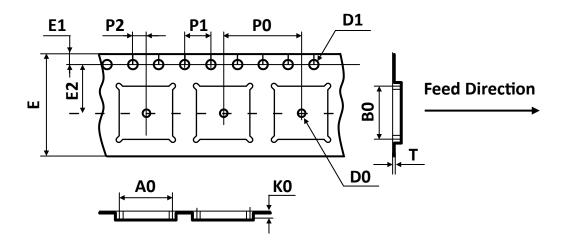


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
16mm	Ø330	±2.00	±0.50	±0.20	+0 50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS ▲ All dimensions in mm

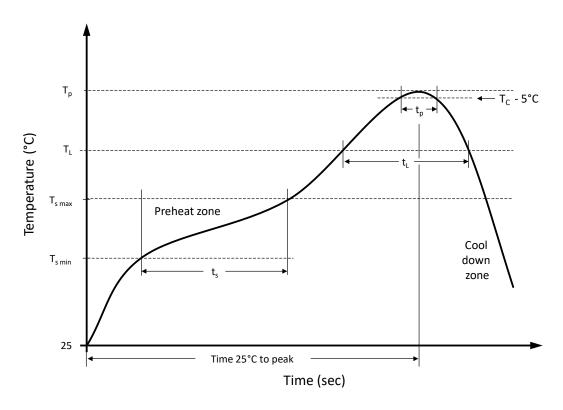


Package	A0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	Т
TO252	6.90	10.50	2.70	1.50	1.50	16.00	1.75	7.50	8.00	4.00	2.00	0.30
(DPAK)	±0.10	±0.10	±0.10	MIN	±0.10	+0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t_L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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